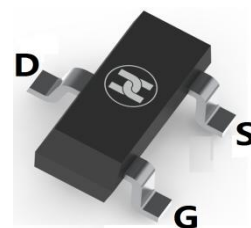
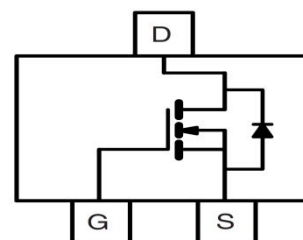


**HIGH VOLTAGE MOSFET (N-CHANNEL)**
**FEATURES**

- Low on-resistance:  $V_{DS}=130V, R_{DS(ON)}=0.75\Omega @ V_{GS}=10V, I_D=1.0A$
- Low Input Capacitance
- Fast Switching Speed
- Low Gate Threshold Voltage
- Surface Mount device


**SOT-23**

**MECHANICAL DATA**

- Case: SOT-23
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.008 grams (approximate)

**MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	100	V
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Continuous drain current	$I_D$	1.0	A
Pulsed drain current (10 $\mu\text{s}$ Pulse, Duty Cycle $\leq 1\%$ )	$I_{DM}$	3.3	A
Maximum Body Diode Continuous Current	$I_S$	1.0	A
Power dissipation	$P_D$	1.26	W
Thermal resistance from Junction to ambient	$R_{\theta JA}$	163	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	17.3	$^\circ\text{C/W}$
Junction temperature	$T_J$	150	$^\circ\text{C}$
Storage temperature	$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
<b>STATIC CHARACTERISTICS</b>						
Drain-Source breakdown voltage	$V_{(BR)DSS}$	130			V	$V_{GS}=0V, I_D=250\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$			100	nA	$V_{DS}=120V, V_{GS}=0V$
Gate-body leakage current	$I_{GSS}$			$\pm 100$	nA	$V_{DS}=0V, V_{GS}=\pm 20V$
Gate-threshold voltage (note 1)	$V_{GS(th)}$	2.0	2.7	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$
Drain-source on-resistance (note 1)	$R_{DS(ON)}$		410	750	m $\Omega$	$V_{GS}=10V, I_D=2.0A$
			430	850	m $\Omega$	$V_{GS}=6.0V, I_D=2.0A$
Diode forward voltage (note 1)	$V_{SD}$		0.8	1.2	V	$I_S=1.0A, V_{GS}=0V$
<b>DYNAMIC CHARACTERISTICS</b>						
Input capacitance	$C_{iss}$		231		pF	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$
Output capacitance	$C_{oss}$		19		pF	
Reverse transfer capacitance	$C_{rss}$		11		pF	
Gate Resistance	$R_g$		2.3		$\Omega$	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$
Total gate charge	$Q_g$		5.6		nC	$V_{DS}=104V, V_{GS}=10V, I_D=2.0A$
Gate-source charge	$Q_{gs}$		0.8		nC	
Gate-drain charge	$Q_{gd}$		2.0		nC	
Turn-on delay time	$t_{d(on)}$		2.3		nS	$V_{DS}=65V, V_{GS}=10V, R_{GEN}=6.0\Omega, I_D=2.0A$
Turn-on rise time	$t_r$		1.7		nS	
Turn-off delay time	$t_{d(off)}$		6.6		nS	
Turn-off fall time	$t_f$		1.7		nS	
Reverse Recovery Time	$t_{rr}$		26		nS	$I_F=1.0A, dI/dt=100A/\mu\text{s}, V_R=100V$
Reverse Recovery Charge	$Q_{rr}$		21		nC	

Note: 1. Pulse test

**HIGH VOLTAGE MOSFET (N-CHANNEL)**

**Typical Characteristics**

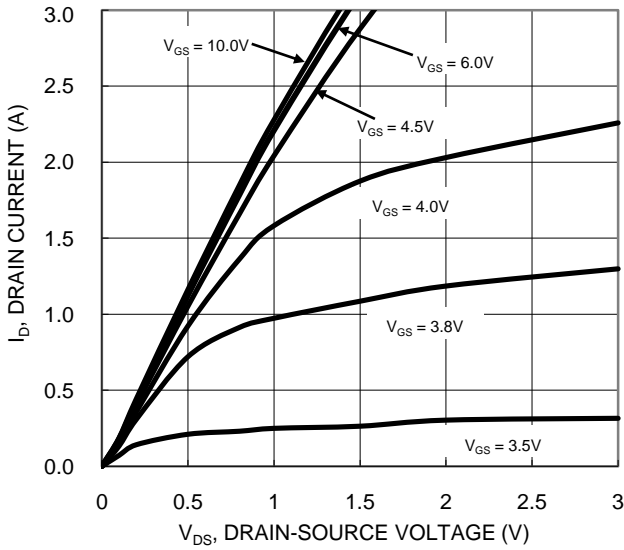


Figure 1. Typical Output Characteristic

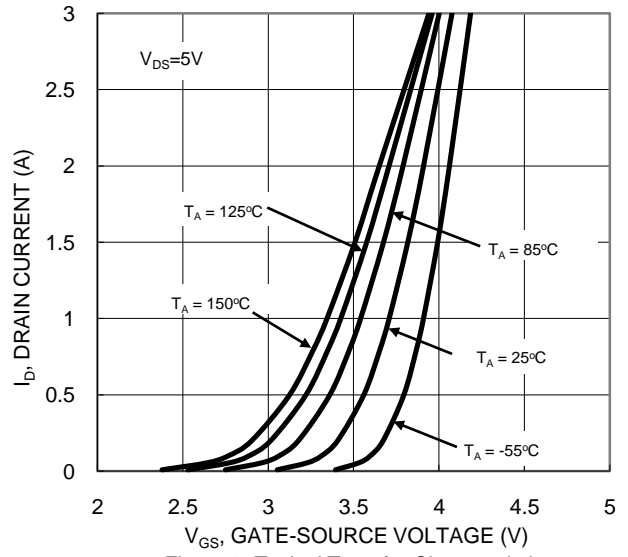


Figure 2. Typical Transfer Characteristic

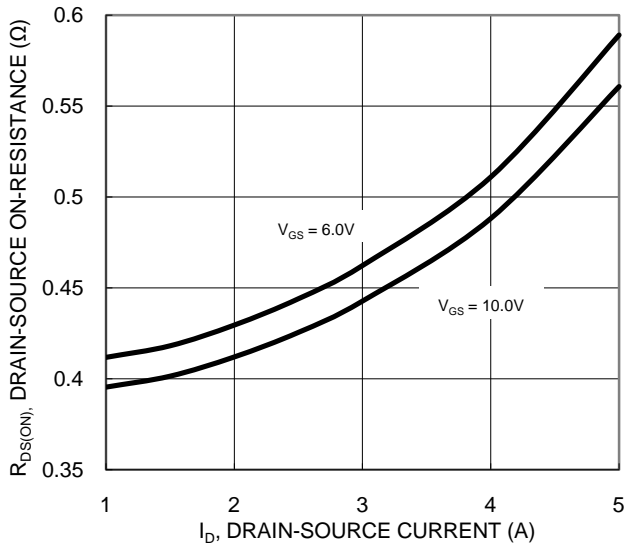


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

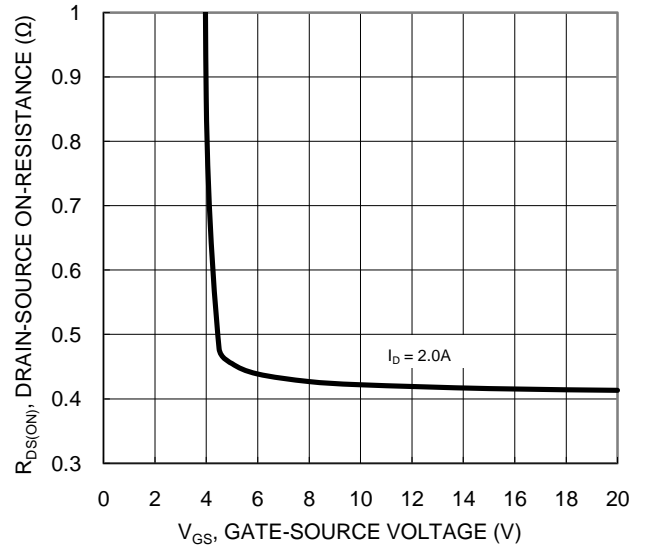


Figure 4. Typical Transfer Characteristic

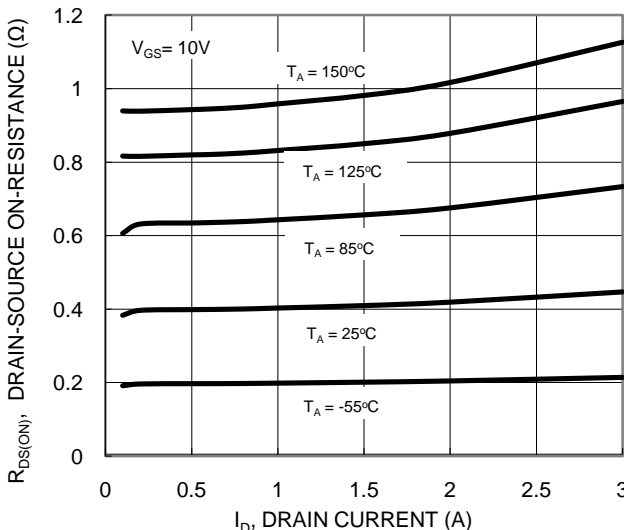


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

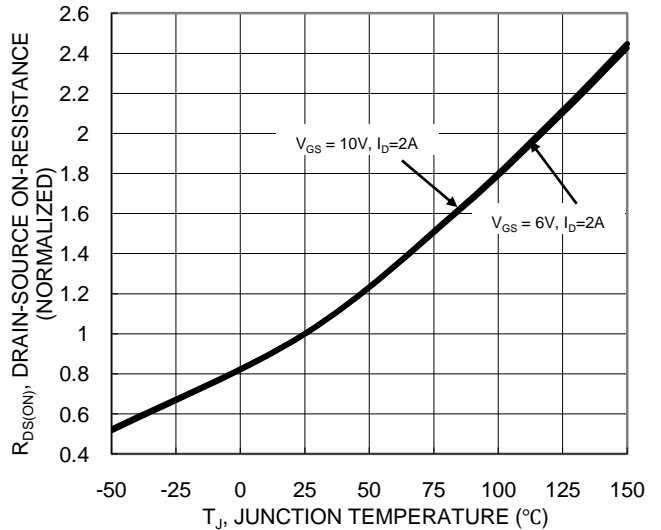


Figure 6. On-Resistance Variation with Temperature

**HIGH VOLTAGE MOSFET (N-CHANNEL)**

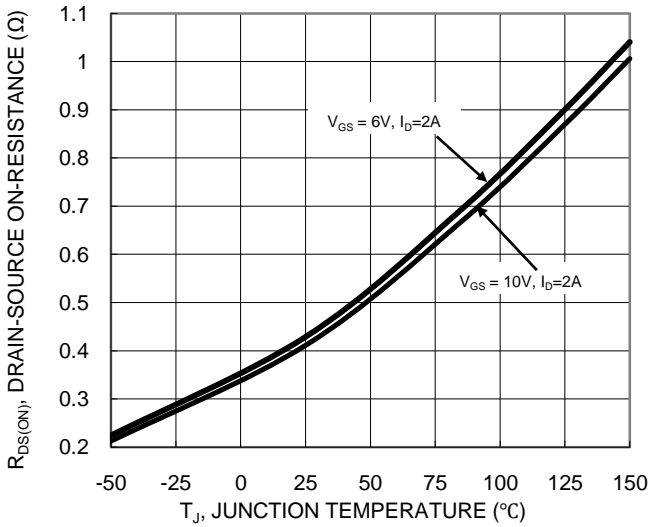


Figure 7. On-Resistance Variation with Temperature

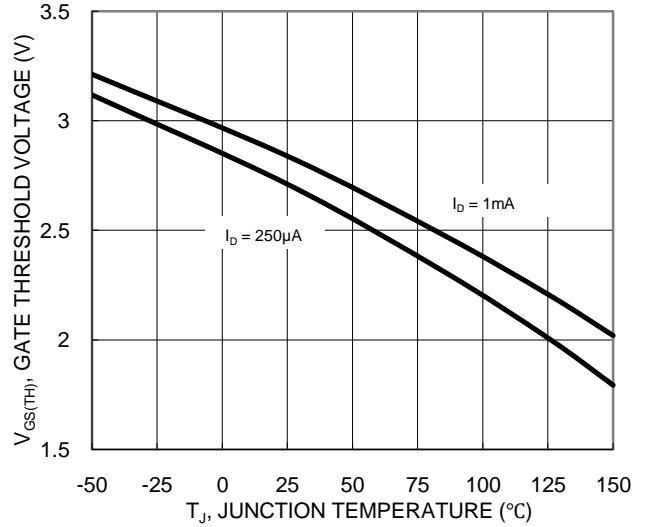


Figure 8. Gate Threshold Variation vs. Junction Temperature

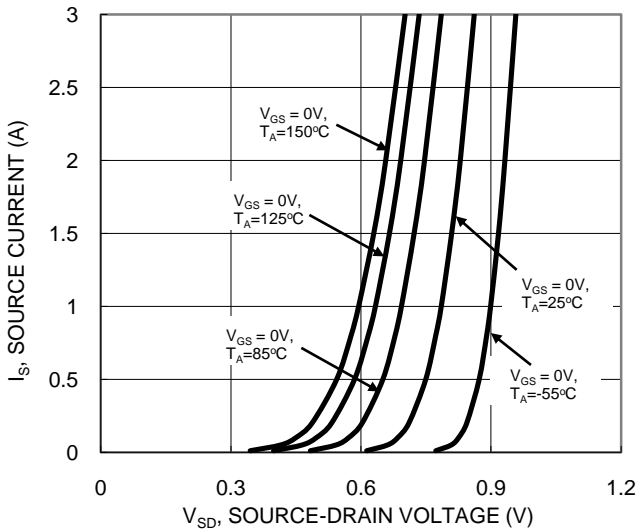


Figure 9. Diode Forward Voltage vs. Current

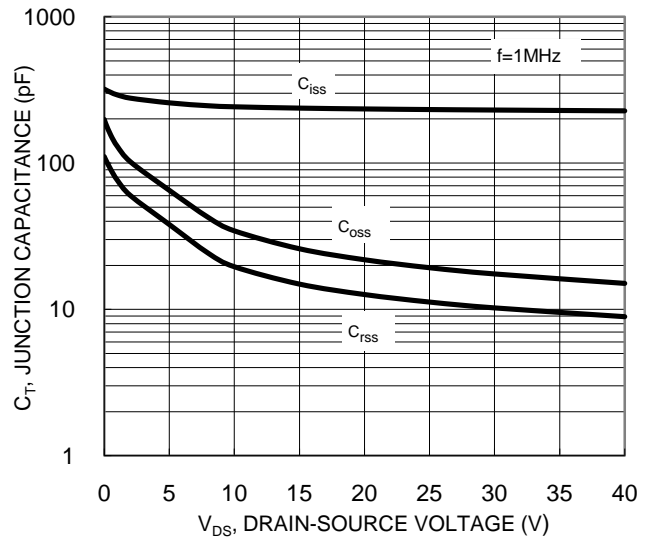


Figure 10. Typical Junction Capacitance

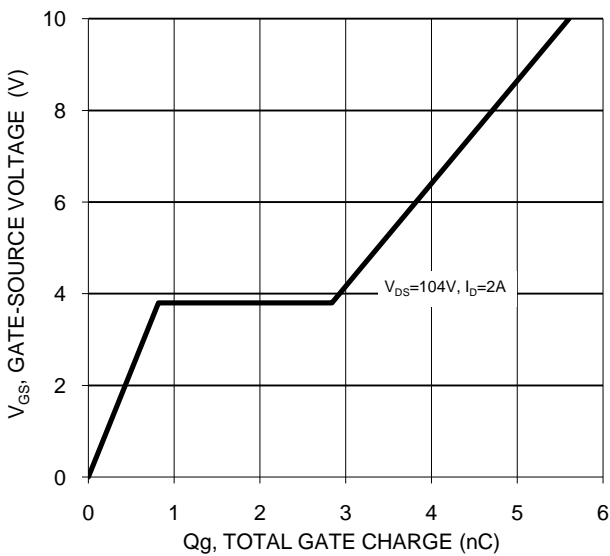


Figure 11. Gate Charge

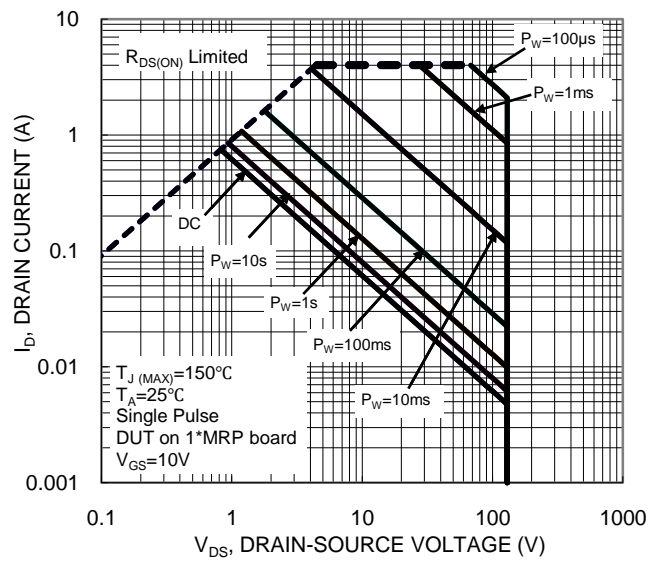


Figure 12. SOA, Safe Operation Area

**HIGH VOLTAGE MOSFET (N-CHANNEL)**

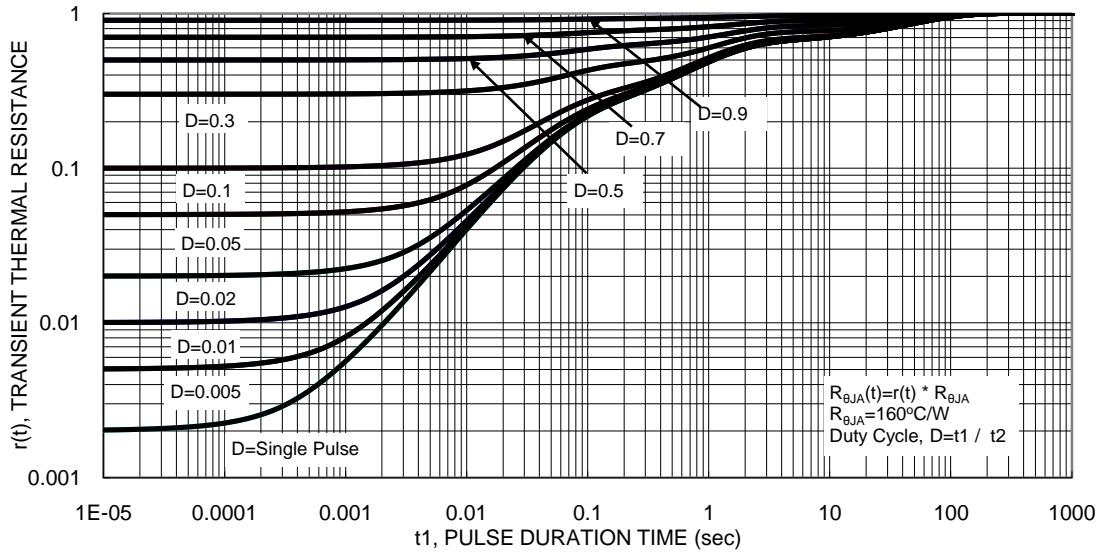
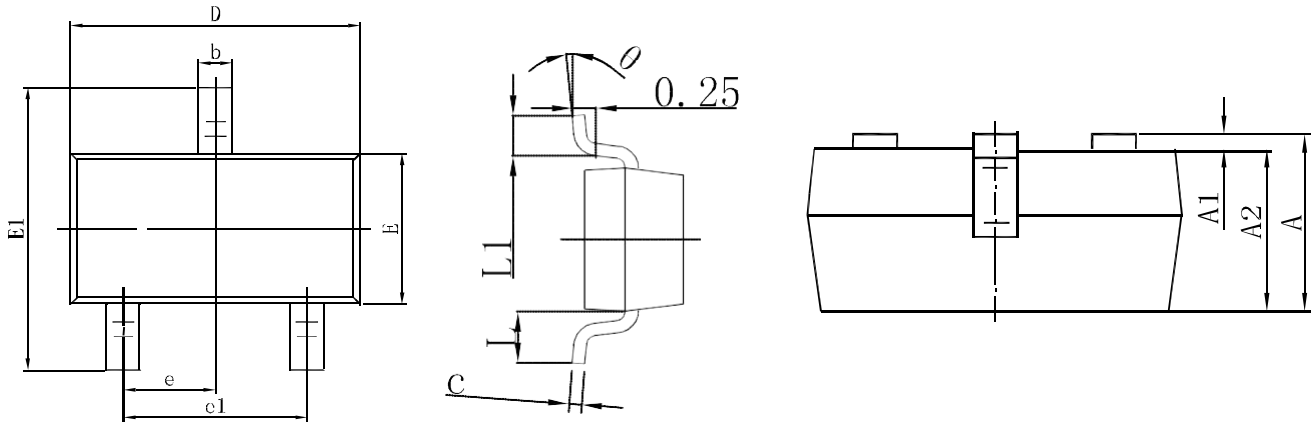
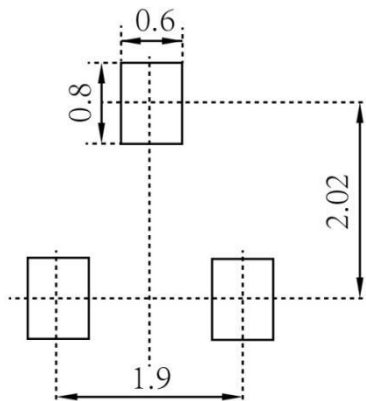


Figure 13. Transient Thermal Resistance

**HIGH VOLTAGE MOSFET (N-CHANNEL)**
**SOT-23 Package Outline Dimensions**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

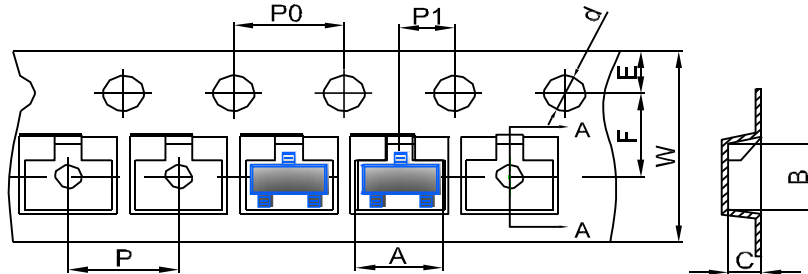
**SOT-23 Suggested Pad Layout**

**Note:**

1. Controlling dimension: in millimeters
2. General tolerance:  $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

HIGH VOLTAGE MOSFET (N-CHANNEL)

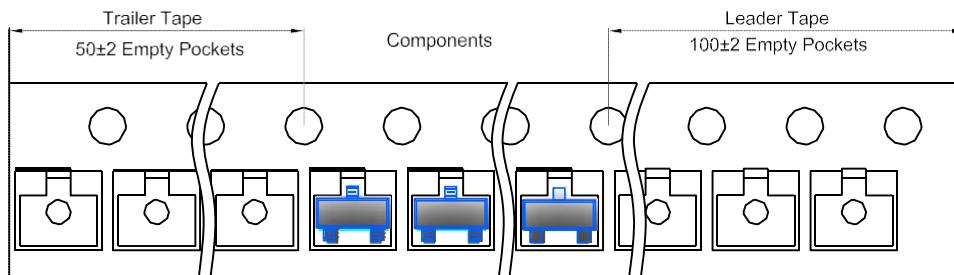
SOT-23 Tape and Reel

SOT-23 Embossed Carrier Tape

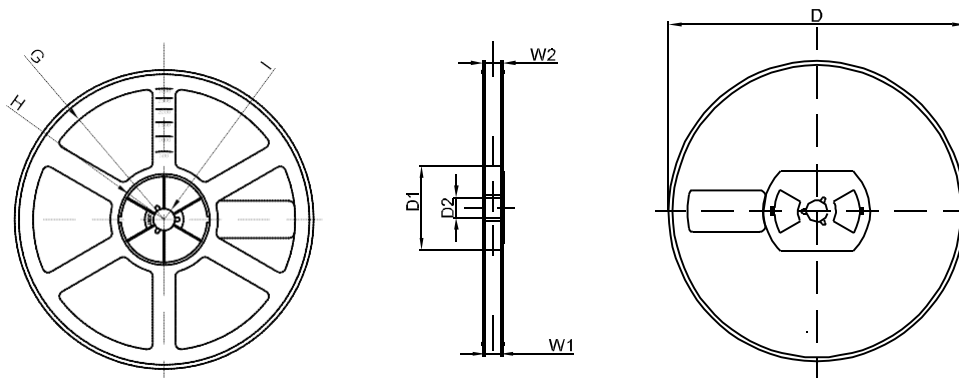


DIMENSIONS ARE IN MILLIMETER										
TYPE	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00
TOLERANCE	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1

SOT-23 Tape Leader and Trailer



SOT-23 Reel



DIMENSIONS ARE IN MILLIMETER								
REEL OPTION	D	D1	D2	G	H	I	W1	W2
7" DIA	Ø178	54.40	13.00	R78	R25.60	R6.50	9.50	12.30
TOLERANCE	±2	±1	±1	±1	±1	±1	±1	±1